

L Number	Hits	Search Text	DB	Time stamp
-	513	348/308.ccls.	USPAT; US-PGPUB; EPO; JPO	2004/08/27 08:31
-	324	348/308.ccls. and @ad<20000222	USPAT; US-PGPUB; EPO; JPO	2004/08/27 08:32
-	24	348/308.ccls. and initiali\$7 and @ad<20000222	USPAT; US-PGPUB; EPO; JPO	2004/08/24 11:27
-	454	photosensor with voltage and capacitor and @ad<20000222	USPAT; US-PGPUB; EPO; JPO	2004/08/24 11:28
-	119	photosensor with voltage with capacitor and @ad<20000222	USPAT; US-PGPUB; EPO; JPO	2004/08/24 11:28
-	33	photosensor near3 voltage with capacitor and @ad<20000222	USPAT; US-PGPUB; EPO; JPO	2004/08/24 11:35
-	0	photosensor near3 voltage near4 (held constant) with capacitor and @ad<20000222	USPAT; US-PGPUB; EPO; JPO	2004/08/24 11:36
-	11812	voltage near4 (held constant) with capacitor and @ad<20000222	USPAT; US-PGPUB; EPO; JPO	2004/08/24 11:36
-	319	(CMOS MOS MOSFET "image sensor" imager "image pickup" pickup) with voltage near4 (held constant) with capacitor and @ad<20000222	USPAT; US-PGPUB; EPO; JPO	2004/08/30 15:18
-	107	(CMOS MOS MOSFET "image sensor" imager "image pickup" pickup) near4 voltage near4 (held constant) with capacitor and @ad<20000222	USPAT; US-PGPUB; EPO; JPO	2004/08/26 10:22
-	68	(CMOS MOS MOSFET "image sensor" imager "image pickup" pickup) near3 voltage near3 (held constant) with capacitor and @ad<20000222	USPAT; US-PGPUB; EPO; JPO	2004/08/24 11:38
-	648	(photosensor photodiode diode) near3 voltage near3 (held constant) with capacitor and @ad<20000222	USPAT; US-PGPUB; EPO; JPO	2004/08/24 11:38
-	10	(photosensor photodiode) near3 voltage near3 (held constant) with capacitor and @ad<20000222	USPAT; US-PGPUB; EPO; JPO	2004/08/25 08:55
-	1	"20010015831"	USPAT; US-PGPUB; EPO; JPO	2004/08/30 14:01
-	2391	(CMOS MOS MOSFET "image sensor" imager "image pickup" pickup) near4 voltage with capacitor and @ad<20000222	USPAT; US-PGPUB; EPO; JPO	2004/08/26 10:22
-	30	(CMOS MOS MOSFET) near4 ("image sensor" imager "image pickup" pickup) with capacitor and @ad<20000222	USPAT; US-PGPUB; EPO; JPO	2004/08/26 10:23
-	1	"20010015831" and drained	USPAT; US-PGPUB; EPO; JPO	2004/08/26 10:41
-	160	348/308.ccls. and (CMOS n-MOS) and @ad<20000222	USPAT; US-PGPUB; EPO; JPO	2004/08/26 11:23
-	2	348/308.ccls. and (CMOS n-MOS) and (four) near5 phase and @ad<20000222	USPAT; US-PGPUB; EPO; JPO	2004/08/26 12:03
-	1003	(CMOS n-MOS) and (four) near5 phase and @ad<20000222	USPAT; US-PGPUB; EPO; JPO	2004/08/26 12:04
-	0	(CMOS n-MOS) and (four) near5 phase with initiali\$7 with exposure and @ad<20000222	USPAT; US-PGPUB; EPO; JPO	2004/08/26 12:05
-	10	(CMOS n-MOS) and (four) near5 phase with initiali\$7 and @ad<20000222	USPAT; US-PGPUB; EPO; JPO	2004/08/26 13:07

-	3	(CMOS n-MOS) and (four) near5 step with initiali\$7 and @ad<20000222	USPAT; US-PGPUB; EPO; JPO	2004/08/26 13:22
-	1	"20010015831" and (charge carriers)	USPAT; US-PGPUB; EPO; JPO	2004/08/26 16:11
-	295	348/302.ccls.	USPAT; US-PGPUB; EPO; JPO	2004/08/27 08:32
-	212	348/302.ccls. and @ad<20000222	USPAT; US-PGPUB; EPO; JPO	2004/08/27 08:37
-	43	(348/308 348/302).ccls. and ("floating diffusion" "memory node") and @ad<20000222	USPAT; US-PGPUB; EPO; JPO	2004/08/27 14:55
-	18	(348/308 348/302).ccls. and ("floating diffusion" "memory node") and (FET n-MOS MOSFET) and @ad<20000222	USPAT; US-PGPUB; EPO; JPO	2004/08/27 13:29
-	29	(348/308 348/302).ccls. and photodiode near4 well and @ad<20000222	USPAT; US-PGPUB; EPO; JPO	2004/08/27 11:52
-	9	(348/308 348/302).ccls. and photodiode near4 (n-well "n- well") and @ad<20000222	USPAT; US-PGPUB; EPO; JPO	2004/08/27 13:24
-	6	(348/308 348/302).ccls. and five near4 transistor and @ad<20000222	USPAT; US-PGPUB; EPO; JPO	2004/08/27 13:24
-	18	(348/308 348/302).ccls. and ("floating diffusion" "memory node") and (FET n-MOS MOSFET) and (reset initiali\$7) and @ad<20000222	USPAT; US-PGPUB; EPO; JPO	2004/08/27 13:31
-	14	(348/308 348/302).ccls. and ("floating diffusion" "memory node") and (photoptransistor photodiode) near4 (reset initiali\$7) and @ad<20000222	USPAT; US-PGPUB; EPO; JPO	2004/08/27 13:33
-	110	(348/308 348/302).ccls. and (CMOS MOSFET FET n-MOS) and (photoptransistor photodiode "floating diffusion" "memory node") near4 (reset initiali\$7) and @ad<20000222	USPAT; US-PGPUB; EPO; JPO	2004/08/27 13:36
-	9	(348/308 348/302).ccls. and (CMOS MOSFET FET n-MOS) and ((photoptransistor photodiode) and ("floating diffusion" "memory node")) near4 (reset initiali\$7) and @ad<20000222	USPAT; US-PGPUB; EPO; JPO	2004/08/27 13:42
-	287	(348/308 348/302).ccls. and (CMOS MOSFET FET n-MOS) and @ad<20000222	USPAT; US-PGPUB; EPO; JPO	2004/08/27 13:43

-	0	(348/308 348/302).ccls. and (CMOS MOSFET FET n-MOS) and @ad<20000222 not (((348/308 348/302).ccls. and five near4 transistor and @ad<20000222) ((348/308 348/302).ccls. and ("floating diffusion" "memory node") and (FET n-MOS MOSFET) and (reset initiali\$7) and @ad<20000222) ((348/308 348/302).ccls. and ("floating diffusion" "memory node") and (photoptransistor photodiode) near4 (reset initiali\$7) and @ad<20000222) ((348/308 348/302).ccls. and (photoptransistor photodiode "floating diffusion" "memory node") near4 (reset initiali\$7) and @ad<20000222) ((348/308 348/302).ccls. and (CMOS MOSFET FET n-MOS) and (photoptransistor photodiode "floating diffusion" "memory node") near4 (reset initiali\$7) and @ad<20000222) ((348/308 348/302).ccls. and (CMOS MOSFET FET n-MOS) and ((photoptransistor photodiode) and ("floating diffusion" "memory node")) near4 (reset initiali\$7) and @ad<20000222) ((348/308 348/302).ccls. and (CMOS MOSFET FET n-MOS) and @ad<20000222))	USPAT; US-PGPUB; EPO; JPO	2004/08/27 13:43
-	173	(348/308 348/302).ccls. and (CMOS MOSFET FET n-MOS) and @ad<20000222 not (((348/308 348/302).ccls. and five near4 transistor and @ad<20000222) ((348/308 348/302).ccls. and ("floating diffusion" "memory node") and (FET n-MOS MOSFET) and (reset initiali\$7) and @ad<20000222) ((348/308 348/302).ccls. and ("floating diffusion" "memory node") and (photoptransistor photodiode) near4 (reset initiali\$7) and @ad<20000222) ((348/308 348/302).ccls. and (photoptransistor photodiode "floating diffusion" "memory node") near4 (reset initiali\$7) and @ad<20000222) ((348/308 348/302).ccls. and (CMOS MOSFET FET n-MOS) and (photoptransistor photodiode "floating diffusion" "memory node") near4 (reset initiali\$7) and @ad<20000222) ((348/308 348/302).ccls. and (CMOS MOSFET FET n-MOS) and ((photoptransistor photodiode) and ("floating diffusion" "memory node")) near4 (reset initiali\$7) and @ad<20000222))	USPAT; US-PGPUB; EPO; JPO	2004/08/27 14:32
-	124	(348/308 348/302).ccls. and (photoptransistor photodiode "floating diffusion" "memory node") near4 (reset initiali\$7) and @ad<20000222	USPAT; US-PGPUB; EPO; JPO	2004/08/27 14:54
-	311	(348/308 348/302).ccls. and ("floating diffusion" "memory node" capacitor) and @ad<20000222	USPAT; US-PGPUB; EPO; JPO	2004/08/27 14:55
-	478	(348/308 348/302).ccls. and @ad<20000222	USPAT; US-PGPUB; EPO; JPO	2004/08/30 09:35
-	268	fossum.in.	USPAT; US-PGPUB; EPO; JPO	2004/08/30 09:35
-	83	fossum.in. and photodiode	USPAT; US-PGPUB; EPO; JPO	2004/08/30 09:36
-	38	fossum.in. and photodiode and @ad<20000222	USPAT; US-PGPUB; EPO; JPO	2004/08/30 09:37
-	0	6667768.URPN.	USPAT	2004/08/30 09:36
-	182	fossum.in. and @ad<20000222	USPAT; US-PGPUB; EPO; JPO	2004/08/30 09:44

-	73	(eric and fossum).in. and @ad<20000222	USPAT; US-PGPUB; EPO; JPO	2004/08/30 10:03
-	39	5665959.URPN.	USPAT	2004/08/30 09:58
-	0	6667768.urpn.	USPAT; US-PGPUB; EPO; JPO	2004/08/30 10:03
-	1	6667768.pn.	USPAT; US-PGPUB; EPO; JPO	2004/08/30 10:03
-	37	("4369378" "4644572" "4684800" "4686648" "4744623" "4776925" "4839735" "4920069" "5054040" "5055900" "5080214" "5105277" "5236871" "5343297" "5386128" "5471515" "5548773" "5665959" "5793322" "5841126" "5872371" "5880691" "5886659" "5887049" "5909026" "5920345" "5949483" "5952645" "5990506" "5995163" "6005619" "6008486" "6021172" "6057539" "6137100" "6166768" "6201270").PN.	USPAT	2004/08/30 10:03